Mid 1 RC Part 3: Static Electric Fields

Conductors and dielectrics in static electric field 1

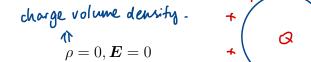
• conductors:

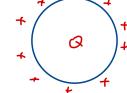
- * current could be in any direction.
- electrons migrate easily.
- charges reach the surface and conductor redistribute the charges in a way that the field vanishes.

- static state conditions:

conservativeness

* inside the conductor:

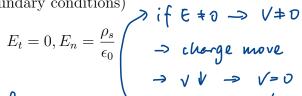


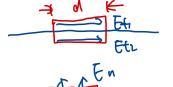


Eti-d + Eti-d + 0 = 0 Eti = - Etz

where $\rho = 0$ represents no charge in the interior

* on the conductor surface (boundary conditions)



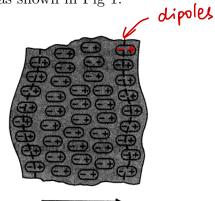


It is an equal-potential body.

$$En \cdot S = \frac{fs \cdot S}{S_0} \implies En = \frac{fs}{S_0}$$

semiconductors:

- relatively small number of freely movable charges.
- insulators(dielectrics):
 - electrons are confined to their orbits.
 - external electric field polarizes a dielectric material and create electric dipoles. The induced electric dipoles will modify the electric field both inside and outside the dielectric material, as shown in Fig 1.



Findne: electric field by included charges.

External E

Figure 1: A cross section of a polarized dielectric medium



- polarization charge densities/ bound-charge densities:
 - * polarization vector, P:

$$oldsymbol{P} = \lim_{\Delta v o 0} rac{\sum_{k=1}^{n \Delta v} oldsymbol{p_k}}{\Delta v}$$

where the numerator represents the vector sum of the induced dipole moment contained in a very small volume Δv .

* charge distribution on surface density:

ne
$$\Delta v$$
.

density:
$$\rho_{ps} = P \cdot a_n$$
sity:
$$P = A \cdot a \cdot s \cdot v$$

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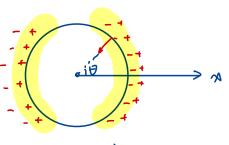
* volume charge distribution density:

$$ho_p = -
abla \cdot oldsymbol{P}$$

$$P \cdot \overrightarrow{A} \cdot \overrightarrow{an} \cdot S = \sum_{q \in \overrightarrow{A}} q \cdot \overrightarrow{A}$$

$$P \cdot \overrightarrow{an} = \sum_{q \in \overrightarrow{A}} q \cdot \overrightarrow{A}$$

 $\rho_p = -\nabla \cdot \mathbf{P}$ $\mathbf{P} \cdot \mathbf{a} \cdot \mathbf{n} \cdot \mathbf{S} = \sum_{\mathbf{q}} \mathbf{q} \cdot \mathbf{a}$ $\mathbf{Ex.1} \text{ Determine the electric field intensity at the center of a small spherical cavity cut}$ of a large block of dielectric in which a polarization \mathbf{P} exists out of a large block of dielectric in which a polarization P exists.



Assume
$$\vec{P} = \vec{a}_{x} \cdot \vec{p}$$

$$P_{ps}(\theta) = \vec{P} \cdot \vec{a}_n$$
 from dielectrics
 $= \vec{P} \cdot \vec{a}_x \cdot \vec{a}_u$

$$dS = 2\pi \cdot \Gamma \cdot \sin\theta \cdot \Gamma \cdot d\theta$$

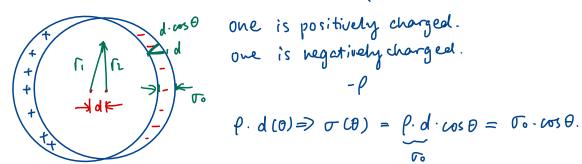
$$dG = dS \cdot Pps(\theta) = -P\cos\theta \cdot 2\pi\Gamma \cdot \sin\theta \cdot \Gamma \cdot d\theta$$

$$dE = \frac{1}{4\pi\Sigma_0} \frac{dq}{\Gamma}$$

$$dE_X = dE \cdot \cos\theta = \frac{P\cos^2\theta \sin\theta}{2\Sigma} d\theta$$

$$E = \int_0^{\pi} dE_X = \frac{P}{3\Sigma_0}.$$





$$\bar{E}_{+} = \frac{1}{4\pi s_{0}} \frac{0}{|\vec{r}_{1}|^{3}} \hat{\Gamma}_{1}$$

$$= \frac{1}{24\pi s_{0}} \frac{3}{3} \ln |\vec{\lambda}|^{3} \cdot \vec{r}_{1}$$

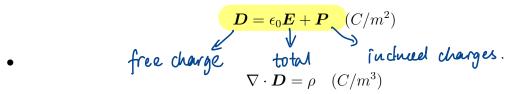
$$= \frac{\rho}{3 s_{0}} \hat{\Gamma}_{1}$$

$$\overline{G}_{-} = -\frac{\rho}{380} \overrightarrow{V}_{2}$$

$$E_{+} + E_{-} = \frac{\rho}{3 \mathcal{L}} (\vec{r}_{1} - \vec{r}_{2}) = \frac{\rho \vec{u}}{3 \mathcal{L}} = \frac{\sigma_{6}}{3 \mathcal{L}} \cdot \frac{\vec{d}}{|\vec{u}|}$$

2 Electric Flux Density and Dielectric Constant

• electric flux density/electric displacement, D:



where ρ is the volume density of free charges.

• Another form of Gauss's law:

$$\oint_{S} \mathbf{D} \cdot d\mathbf{s} = \underbrace{Q_{free}}_{\mathbf{C}} (\mathbf{C})$$

the total outward flux of the electric displacement (the total outward electric flux) over any closed surface is equal to the total free charge enclosed in the surface.

• If the dielectric of the medium is linear and isotropic,

lium is linear and isotropic,
$$P = \epsilon_0 \chi_e E$$

$$P = \lambda \mathcal{E} \longrightarrow \text{applied field.}$$

$$D = \epsilon_0 (1 + \chi_e) E = \epsilon_0 \epsilon_r E = \epsilon E$$
 dipple moment

where χ_e is a dimensionless quantity called electric susceptibility,

 ϵ_r is a dimensionless quantity called as relative permittivity/ electric constant of the medium,

 ϵ is the absolute permittivity/permittivity of the medium (F/m).

• For anisotropic,

$$\begin{bmatrix} D_x \\ D_y \\ D_z \end{bmatrix} = \begin{bmatrix} \epsilon_{11} & \epsilon_{12} & \epsilon_{13} \\ \epsilon_{21} & \epsilon_{22} & \epsilon_{23} \\ \epsilon_{31} & \epsilon_{32} & \epsilon_{33} \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

For bi-axial,

$$\begin{bmatrix} D_x \\ D_y \\ D_z \end{bmatrix} = \begin{bmatrix} \epsilon_1 & 0 & 0 \\ 0 & \epsilon_2 & 0 \\ 0 & 0 & \epsilon_3 \end{bmatrix} \begin{bmatrix} E_x \\ E_y \\ E_z \end{bmatrix}$$

For uni-axial, $\epsilon_1 = \epsilon_2$, For isotropic, $\epsilon_1 = \epsilon_2 = \epsilon_3$ (the only kind of media we deal with in this course).

• dielectric breakdown: electric field is very strong, causes permanent dislocations and damage in the material.

dielectric strength: the maximum electric field intensity that a dielectric material can withstand without breakdown.

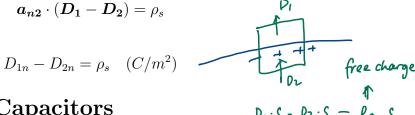
3 Boundary Conditions for Electrostatic Fields

ullet the tangential component of an $m{E}$ field is continuous across an interface.

$$E_{1t}=E_{2t}\quad (V/m)$$

$$\frac{D_{1t}}{\epsilon_1}=\frac{D_{2t}}{\epsilon_2}$$

 \bullet The normal component of D field is discontinuous across an interface where a surface charge exists - the amount of discontinuity being equal to the surface charge density.



or

or

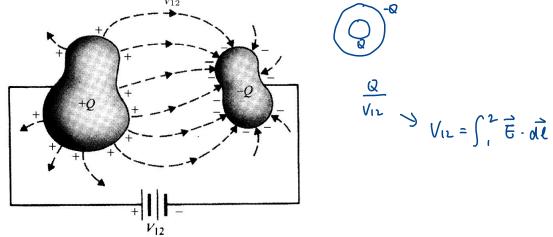
4 Capacitance and Capacitors

4.1 Capacitance

- Definition: The capacitance of isolated conducting body is the electric charge that must be added to the body per unit increase in its electric potential.
- $C = \frac{Q}{V} (F = C/V)$

4.2 Capacitor

• Components: two conductors with arbitrary shapes are separated by free space or dielectric medium. $C = \frac{Q}{V_{12}}$



• Capacitance:

Its Capacitance is independent of V and Q, which means a capacitor has a capacitance even no voltage is applied to it and no free charges exist on its conductors.

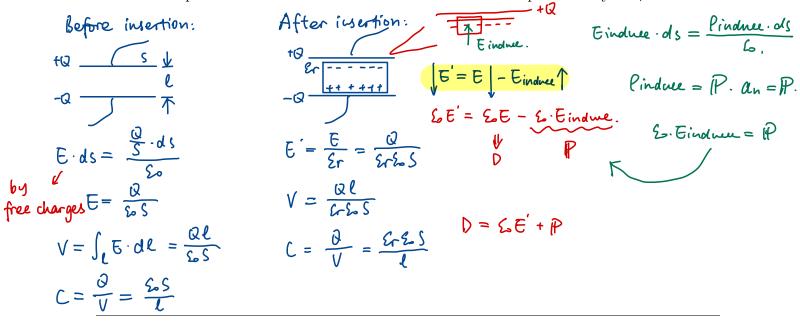
- How to calculate its capacitance:
 - 1. Choose a proper coordinate system
 - 2. Assume +Q, -Q on the conductors
 - 3. Find **E** from Q (like, Gauss's law, $D_n = \epsilon E_n = \rho_s$)
 - 4. Find $V_{12} = -\int_{2}^{1} \mathbf{E} \cdot d\mathbf{l}$
 - 5. $C = Q/V_{12}$
- Series Connections of Capacitors:

$$\frac{1}{C_{sr}} = \frac{1}{C_1} + \frac{1}{C_2} + \ldots + \frac{1}{C_n}$$

• Parallel Connections of Capacitors:

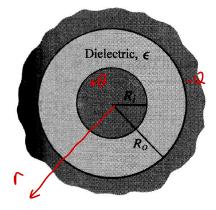
$$C_{||} = C_1 + C_2 + \dots + C_n$$

Ex.2 Suppose we have a parallel conductor plane capacitor with capacitance of C, what is the new capacitance C' if we insert a dielectric with relative permittivity of ϵ_r ?



Please refer to text book instead of this sheet as the standard

Ex.3 A spherical capacitor consists of an inner conducting sphere of radius R_i and an outer conductor with a sphere inner wall of radius R_o . The space in between is filled with a dielectric of permittivity ϵ . Determine the capacitance.



$$\oint \overrightarrow{D} \cdot ds = Q$$

$$\overrightarrow{D} = \frac{Q}{4\pi r^{2}} \widehat{r}$$

$$\overrightarrow{E} = \frac{D}{\xi} = \frac{Q}{4\pi \xi r^{2}} \widehat{r}$$

$$V = \int_{R_{i}}^{R_{i}} \overrightarrow{E} \cdot d\ell = \frac{Q}{4\pi \xi} \left[\frac{1}{R_{i}} - \frac{1}{R_{i}} \right]$$

$$C = \frac{Q}{V} \dots$$

4.3 Electrostatic Energy and Forces

• Potential difference between P_1 to P_2

moving from P1 to P2.
$$= \frac{W_{12}}{q} = V_{21} = V_2 - V_1 = -\int_{P_1}^{P_2} \mathbf{E} \cdot d\mathbf{l}$$

• Self Energy: Work done to bring a charge Q_2 from infinitely far away to distance R_{12} with Q_1 (initially, Q_1 is in space)

$$W = Q_2 V_2 = Q_2 \frac{Q_1}{4\pi\epsilon_0 R_{12}}$$

• Mutual Energy: Potential energy of a group of N discrete point charges at rest



0

$$W_e=rac{1}{2}\sum_{k=1}^N Q_k V_k$$
 why $rac{1}{4}$: without energy is shared by 1 & 2

where $V_k = \frac{1}{4\pi\epsilon_0} \sum_{j=1}^N \sum_{k\neq k} \frac{Q_j}{R_{jk}}$ Note the W_e can be negative, for example, there are 2-point charge systems, and one charge is positive, the other is negative.

- Electrostatic Energy (Volume) density w_e : $W_e = \int_{v'} w_e dv$
- 4.3.1 Electrostatic Energy in terms of Field Quantities
 - v' can be all space.
 - A continuous Charge Distribution of Density ρ $\nabla \cdot \mathcal{D} = \rho$

$$W_e = \frac{1}{2} \int_{v} \rho V dv = \frac{1}{2} \int_{v'} (\nabla \cdot \mathbf{D}) V dv$$

Another expression:

• If it is a simple dielectric, it should be

$$W_e = \frac{1}{2} \int_{v'} \epsilon E^2 dv = \frac{1}{2} \int_{v'} \frac{D^2}{\epsilon} dv$$

4.3.2 Electrostatic Forces

Here we use **Principle of virtual displacement** to calculate Force in two situations.

- System of bodies with fixed charges
 - 1. Mechanical work is from the reduced stored electrostatic energy

$$F_Q = -\nabla W_e(N)$$

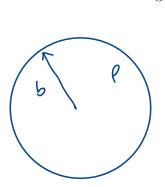
2. Electric torque rotates one of the bodies by $d\phi$ (a virtual rotation) about an axis

$$T_Q = -\frac{\partial W_e}{\partial \phi} (N \cdot m)$$



- System of conducting bodies with Fixed Potentials
 - 1. The fixed potential can be retained by connecting with an external source.
 - 2. $F_v = \nabla W_e$
 - 3. $T_v = \frac{\partial W_e}{\partial \phi}$

Example 3-22 Find the energy required to assemble a uniform sphere of charges of radius b and volume charge ρ .



$$W = \int dW$$

$$= \int V(Q) \cdot dQ$$

$$V = \int_{R} \vec{E} = \frac{Q}{4\pi s_{R}} \hat{\omega}_{r}$$

$$Q = \frac{4}{3}\pi R^{3} \cdot P$$

$$dQ = 4\pi PR^{2} \cdot dR$$